

Mits	Search Text	DBs	Time Stamp
1 1701	(phase adj change) with memory	US-PPGPUB; USPAT; EPO; JPO: DERWENT;	2004/09/22 11:18
2 292	(phase adj change) with memory and "257"/\$.cccls.	US-PPGPUB; USPAT; EPO; JPO: DERWENT;	2004/09/22 15:56
3 14	pram and "257"/\$.cccls.	US-PPGPUB; USPAT; EPO; JPO: DERWENT;	2004/09/22 11:14
4 7848	257/2,4,184,194,200,203,400,421,530,734.cccls. 438/131.cccls. 365/145,175.cccls.	US-PPGPUB; USPAT; EPO; JPO: DERWENT;	2004/09/22 11:19
5 105	((phase adj change) with memory) and (257/2,4,184,194,200,203,400,421,530,734.cccls. 438/131.cccls. 365/145,175.cccls.)	US-PPGPUB; USPAT; EPO; JPO: DERWENT;	2004/09/22 15:56
6 44	((phase adj change) with memory) and (257/2,4,184,194,200,203,400,421,530,734.cccls. 438/131.cccls. 365/145,175.cccls.) and transistor and (source or drain)	US-PPGPUB; USPAT; EPO; JPO: DERWENT;	2005/01/21 15:22
7 0	((phase adj change) with memory) and (257/2,4,184,194,200,203,400,421,530,734.cccls. 438/131.cccls. 365/145,175.cccls.) not (257/2,4,184,194,200,203,400,421,530,734.cccls. 438/131.cccls. 365/145,175.cccls.)	US-PPGPUB; USPAT; EPO; JPO: DERWENT;	2005/01/21 15:23
8 61	((phase adj change) with memory) and (257/2,4,184,194,200,203,400,421,530,734.cccls. 438/131.cccls. 365/145,175.cccls.) not ((phase adj change) with memory) and (257/2,4,184,194,200,203,400,421,530,734.cccls. 438/131.cccls. 365/145,175.cccls.) and transistor and (source or drain)	US-PPGPUB; USPAT; EPO; JPO: DERWENT;	2005/01/21 15:23
9 292	(phase adj change) with memory and "257"/\$.cccls.	US-PPGPUB; USPAT; EPO; JPO: DERWENT;	2004/09/22 15:56
10 105	((phase adj change) with memory) and (257/2,4,184,194,200,203,400,421,530,734.cccls. 438/131.cccls. 365/145,175.cccls.)	US-PPGPUB; USPAT; EPO; JPO: DERWENT;	2004/09/22 15:57
11 199	((phase adj change) with memory and "257"/\$.cccls.) not ((phase adj change) with memory) and (257/2,4,184,194,200,203,400,421,530,734.cccls. 438/131.cccls. 365/145,175.cccls.)	US-PPGPUB; USPAT; EPO; JPO: DERWENT;	2004/09/22 15:57
12 2	"20020036931".pn.	US-PPGPUB; USPAT; EPO; JPO: DERWENT;	2004/09/23 16:21
13 7	((phase adj change) with memory) and (257/2,4,184,194,200,203,400,421,530,734.cccls. 438/131.cccls. 365/145,175.cccls.) and transistor and (source or drain) and @pd>"20040923"	US-PPGPUB; USPAT; EPO; JPO: DERWENT;	2005/01/21 15:22
14 0	((phase adj change) with memory) and (257/2,4,184,194,200,203,400,421,530,734.cccls. 438/131.cccls. 365/145,175.cccls.) not (257/2,4,184,194,200,203,400,421,530,734.cccls. 438/131.cccls. 365/145,175.cccls.) and @pd>"20040923"	US-PPGPUB; USPAT; EPO; JPO: DERWENT;	2005/01/21 15:23
15 8	((phase adj change) with memory) and (257/2,4,184,194,200,203,400,421,530,734.cccls. 438/131.cccls. 365/145,175.cccls.) not ((phase adj change) with memory) and (257/2,4,184,194,200,203,400,421,530,734.cccls. 438/131.cccls. 365/145,175.cccls.) and transistor and (source or drain) and @pd>"20040923"	US-PPGPUB; USPAT; EPO; JPO: DERWENT;	2005/01/21 15:23
16 15	S13 914 915	US-PPGPUB; USPAT; EPO; JPO: DERWENT;	2005/01/21 15:23

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